



Journal of Semiconductor Technology and Science

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March 2006 Special Issue on Nanoscale Semiconductor Devices

Journal of Semiconductor Technology and Science will publish an issue of Nanoscale Semiconductor Devices. It will provide an overview of recent theoretical and experimental progress in the field of *device physics, novel devices, and nanofabrication technology*. It is intended to serve as a vehicle for summarizing and highlighting the major developments that have occurred over past few years.

1. Device Physics

- Transport in low dimensions
- Quantum effects
- Granularity and fluctuations
- Physics of nanoscale memories
- Metal-insulator transition

2. Novel devices

- 3D device structures
- Novel memories
- CNT devices
- Tunneling and single electron devices
- Quantum and cellular networks

3. Nanofabrication Technologies

- Nanolithography
- Nanoimprint
- Self organization
- Nanofabrication process for high performance

Authors wishing to have their contributions considered for publication in this special issue, which will be published in March 2006, are invited to submit an electronic copy of their manuscripts to Editor, Byung-Gook Park, no later than **December 31, 2005**. Manuscripts should be submitted in free style double spaced MS Word format as an email attachment. See <http://www.jsts.org> for detail. Both regular papers as well as letters are welcome.

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